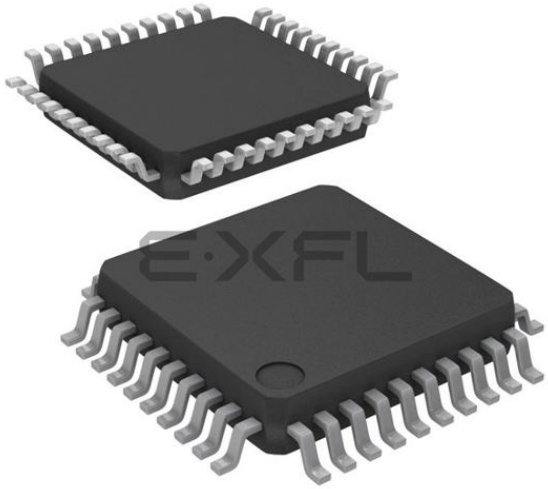
Renesas Electronics America Inc - R5F10RBAAFP#50 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	20
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 4x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10rbaafp-50

1.4 Pin Identification

ANI0, ANI1, ANI16 to ANI23:	Analog Input	P130, P137:	Port 13
		P140 to P147:	Port 14
AV_{REFM}:	Analog Reference Voltage Minus	PCLBUZ0, PCLBUZ1:	Programmable Clock Output/Buzzer Output
AV_{REFP}:	Analog Reference Voltage Plus	REGC:	Regulator Capacitance
		$\overline{RESET}$:	Reset
CAPH, CAPL:	Capacitor for LCD	RTC1HZ:	Real-time Clock Correction Clock (1 Hz) Output
COM0 to COM7,			
EV_{DD}:	Power Supply for Port	RxD0:	Receive Data
EV_{SS}:	Ground for Port	$\overline{SCK00}$, $\overline{SCK01}$:	Serial Clock Input/Output
EXCLK:	External Clock Input (Main System Clock)	SCLA0:	Serial Clock Input/Output
		SDAA0:	Serial Data Input/Output
EXCLKS:	External Clock Input (Subsystem Clock)	SEG0 to SEG38:	LCD Segment Output
		SI00, SI01:	Serial Data Input
INTP0 to INTP7:	Interrupt Request From Peripheral	SO00, SO01:	Serial Data Output
		TI00 to TI07:	Timer Input
KR0 to KR3:	Key Return	TO00 to TO07:	Timer Output
P10 to P17:	Port 1	TOOL0:	Data Input/Output for Tool
P20, P21:	Port 2	TOOLRxD, TOOLTxD:	Data Input/Output for External Device
P30 to P32:	Port 3	TxD0:	Transmit Data
P40 to P43:	Port 4	V_{DD}:	Power Supply
P50 to P54:	Port 5	V_{L1} to V_{L4}:	LCD Power Supply
P60, P61:	Port 6	V_{SS}:	Ground
P70 to P74:	Port 7	X1, X2:	Crystal Oscillator (Main System Clock)
P120 to P127:	Port 12	XT1, XT2:	Crystal Oscillator (Subsystem Clock)

2. ELECTRICAL SPECIFICATIONS (A, G: T_A = -40 to +85°C)

This chapter describes the electrical specifications for the products "A: Consumer applications (T_A = -40 to +85°C)" and "G: Industrial applications (with T_A = -40 to +85°C)".

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. With products not provided with an EV_{DD}, or EV_{SS} pin, replace EV_{DD} with V_{DD}, or replace EV_{SS} with V_{SS}.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high[Note 1]	I_{OH1}	Per pin for P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147				–10.0 [Note 2]	mA
		Total of P10 to P14, P40 to P43, P120, P130, P140 to P147 (When duty = 70% [Note 3])	4.0 V ≤ EV_{DD} ≤ 5.5 V			–40.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			–8.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			–4.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			–2.0	mA
		Total of P15 to P17, P30 to P32, P50 to P54, P70 to P74, P125 to P127 (When duty = 70% [Note 3])	4.0 V ≤ EV_{DD} ≤ 5.5 V			–60.0	mA
			2.7 V ≤ EV_{DD} < 4.0 V			–15.0	mA
			1.8 V ≤ EV_{DD} < 2.7 V			–8.0	mA
			1.6 V ≤ EV_{DD} < 1.8 V			–4.0	mA
		Total of all pins (When duty = 70% [Note 3])				–100.0	mA
	I_{OH2}	P20, P21	Per pin			–0.1	mA
			Total of all pins	1.6 V ≤ V_{DD} ≤ 5.5 V		–0.2	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from the V_{DD} and EV_{DD} pins to an output pin.

2. Do not exceed the total current value.

3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = –40.0 mA

Total output current of pins = (–40.0 × 0.7)/(80 × 0.01) ≅ –35.0 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P10, P12, P15, and P17 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

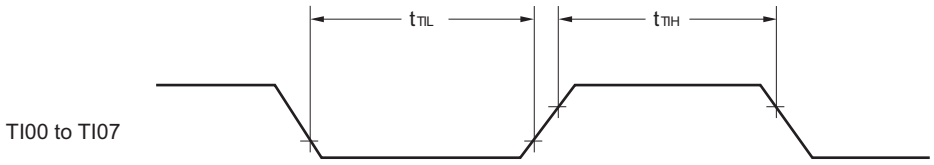
(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V) (4/5)

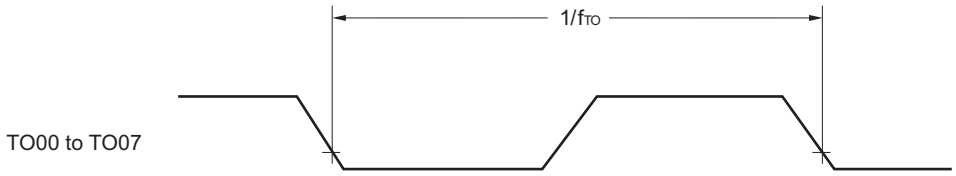
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V_{OH1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –10 mA	EV_{DD}–1.5			V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –3.0 mA	EV_{DD}–0.7			V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –2.0 mA	EV_{DD}–0.6			V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.5 mA	EV_{DD}–0.5			V
			1.6 V ≤ EV_{DD} ≤ 5.5 V, I_{OH1} = –1.0 mA	EV_{DD}–0.5			V
	V_{OH2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OH2} = –100 μA	V_{DD}–0.5			V
Output voltage, low	V_{OL1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P130, P140 to P147	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 20 mA			1.3	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 8.5 mA			0.7	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 3.0 mA			0.6	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 1.5 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL1} = 0.6 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL1} = 0.3 mA			0.4	V
	V_{OL2}	P20, P21	1.6 V ≤ V_{DD} ≤ 5.5 V, I_{OL2} = 400 μA			0.4	V
	V_{OL3}	P60, P61	4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 15.0 mA			2.0	V
			4.0 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 5.0 mA			0.4	V
			2.7 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 3.0 mA			0.4	V
			1.8 V ≤ EV_{DD} ≤ 5.5 V, I_{OL3} = 2.0 mA			0.4	V
			1.6 V ≤ EV_{DD} < 5.5 V, I_{OL3} = 1.0 mA			0.4	V

Caution P10, P12, P15, P17 do not output high level in N-ch open-drain mode.

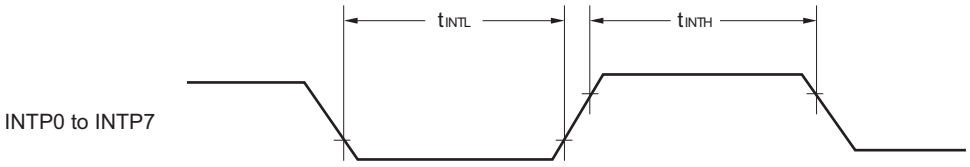
Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

TI/TO Timing

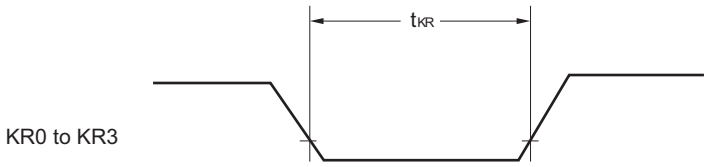




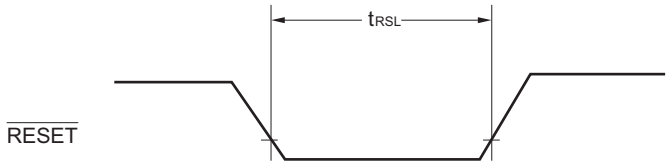
Interrupt Request Input Timing



Key Interrupt Input Timing



$\overline{\text{RESET}}$ Input Timing



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	2.7 V ≤ EV_{DD} ≤ 5.5 V		167 Note 1		500 Note 1		1000 Note 1		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		250 Note 1		500 Note 1		1000 Note 1		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				500 Note 1		1000 Note 1		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						1000 Note 1		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 12		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.7 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 18		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY1}/2 – 38		t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				t_{KCY1}/2 – 50		t_{KCY1}/2 – 50		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						t_{KCY1}/2 – 100		ns
SIp setup time (to SCKp↑) Note 2	t_{SIK1}	2.7 V ≤ EV_{DD} ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				110		110		ns
		1.6 V ≤ EV_{DD} ≤ 5.5 V						220		ns
SIp hold time (from SCKp↑) Note 3	t_{KSI1}	2.4 V ≤ EV_{DD} ≤ 5.5 V		19		19		19		ns
		1.8 V ≤ EV_{DD} ≤ 5.5 V				19		19		
		1.6 V ≤ EV_{DD} ≤ 5.5 V						19		
Delay time from SCKp↓ to SOp output Note 4	t_{KSO1}	C = 30 pF Note 5	2.4 V ≤ EV_{DD} ≤ 5.5 V		25		25		25	ns
			1.8 V ≤ EV_{DD} ≤ 5.5 V				25		25	
			1.6 V ≤ EV_{DD} ≤ 5.5 V						25	

Notes 1. For CSI00, set a cycle of 2/f_{MCK} or longer. For CSI01, set a cycle of 4/f_{MCK} or longer.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(**Remarks** are listed on the next page.)

Remarks 1. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM and POM numbers (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00, 01))

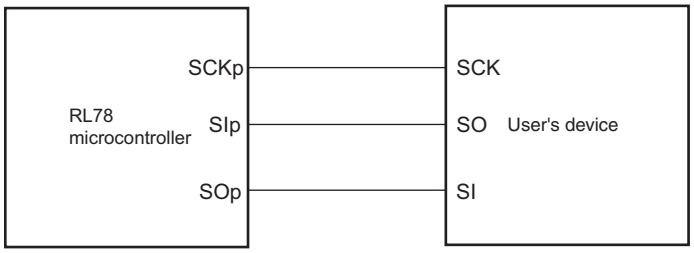
(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

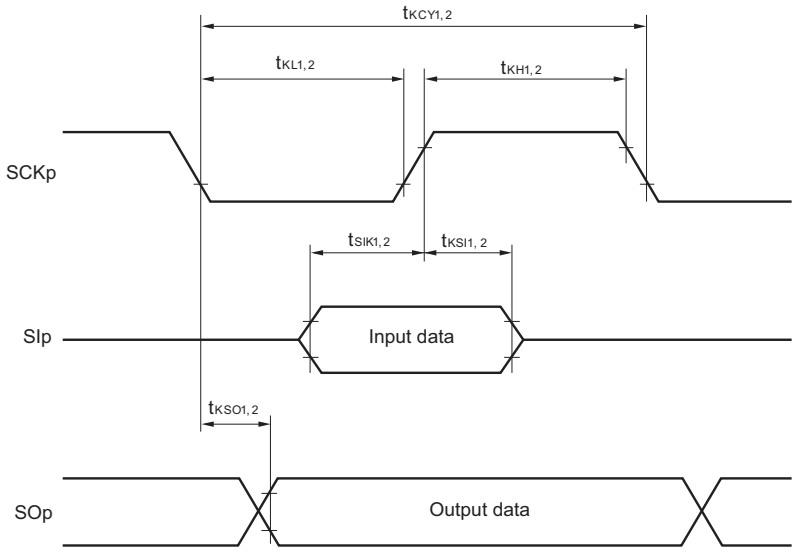
Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time[Note 5]	t_{KCY2}	4.0 V ≤ EV_{DD} ≤ 5.5 V	20 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 20 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.7 V ≤ EV_{DD} < 4.0 V	16 MHz < f_{MCK}	8/f_{MCK}						ns
			f_{MCK} ≤ 16 MHz	6/f_{MCK}		6/f_{MCK}		6/f_{MCK}		ns
		2.4 V ≤ EV_{DD} ≤ 5.5 V		6/f_{MCK} and 500		6/f_{MCK}		6/f_{MCK}		ns
		1.8 V ≤ EV_{DD} < 2.4 V				6/f_{MCK}		6/f_{MCK}		ns
		1.6 V ≤ EV_{DD} < 1.8 V						6/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD} ≤ 5.5 V		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		t_{KCY2}/2 – 7		ns
		2.7 V ≤ EV_{DD} < 4.0 V		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		t_{KCY2}/2 – 8		ns
		2.4 V ≤ EV_{DD} < 2.7 V		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.8 V ≤ EV_{DD} < 2.4 V				t_{KCY2}/2 – 18		t_{KCY2}/2 – 18		ns
		1.6 V ≤ EV_{DD} < 1.8 V						t_{KCY2}/2 – 66		ns
SIp setup time (to SCKp↑)[Note 1]	t_{SIK2}	2.7 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 20		1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		2.4 V ≤ EV_{DD} < 2.7 V		1/f_{MCK} + 30		1/f_{MCK} + 30		1/f_{MCK} + 30		
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 30		1/f_{MCK} + 30		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 40		ns
SIp hold time (from SCKp↑)[Note 2]	t_{KSI2}	2.4 V ≤ EV_{DD} ≤ 5.5 V		1/f_{MCK} + 31		1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.8 V ≤ EV_{DD} < 2.4 V				1/f_{MCK} + 31		1/f_{MCK} + 31		ns
		1.6 V ≤ EV_{DD} < 1.8 V						1/f_{MCK} + 250		ns

(**Notes**, **Caution,** and **Remarks** are listed on the next page.)

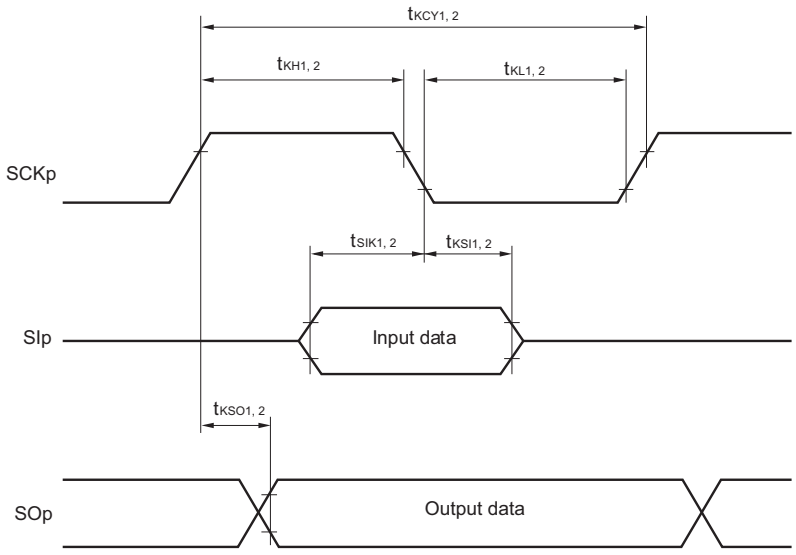
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



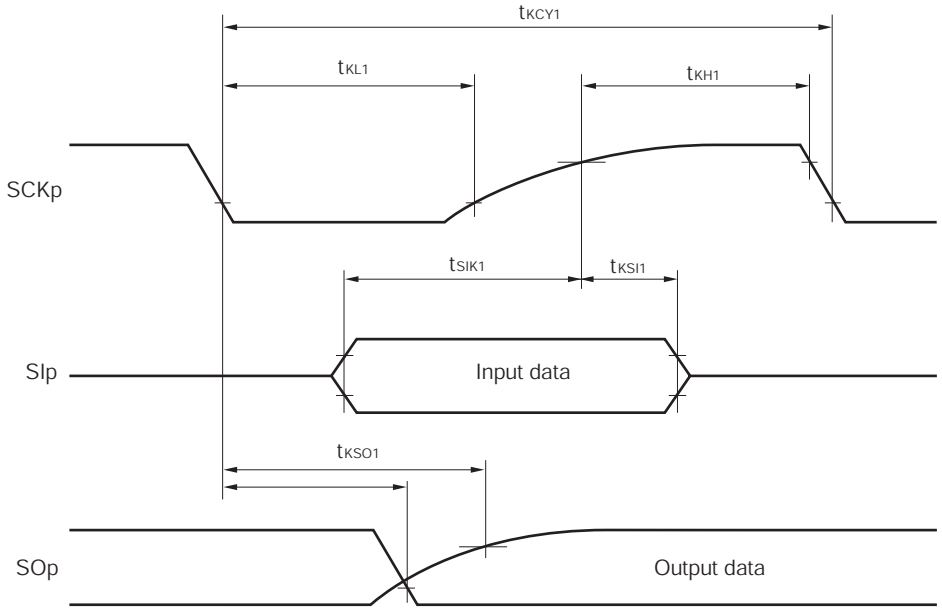
CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



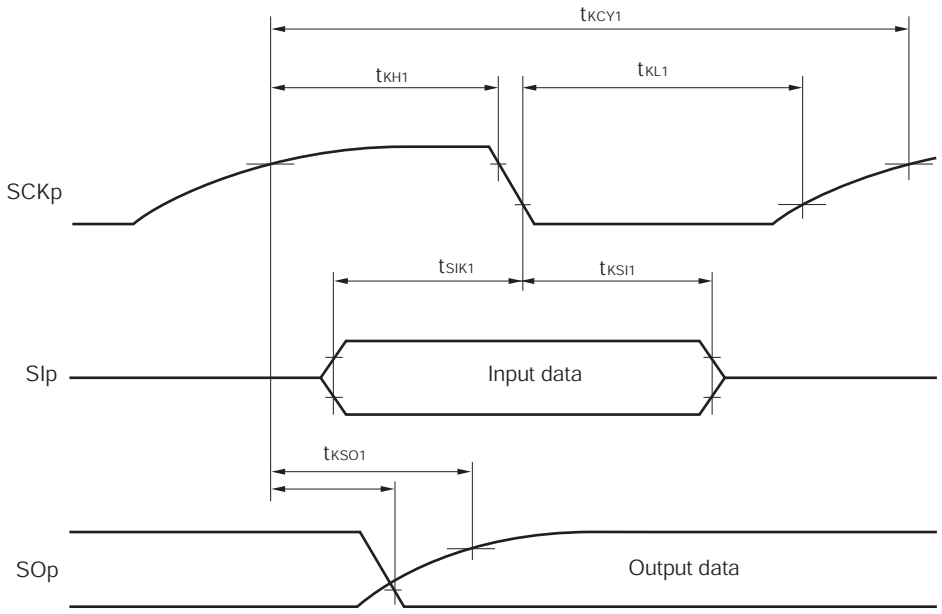
Remarks 1. p: CSI number (p = 00, 01)

2. m: Unit number, n: Channel number (mn = 00, 01)

CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),
g: PIM and POM number (g = 1)

(3) I^2C fast mode plus

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode plus: f_{CLK} ≥ 10 MHz	2.7 V ≤ EV_{DD} ≤ 5.5 V	0	1000	—		—		kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.26		—		—		μs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.26		—		—		μs
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.5		—		—		μs
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.26		—		—		μs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		50		—		—		μs
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0	0.45	—		—		μs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.26		—		—		μs
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD} ≤ 5.5 V		0.5		—		—		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

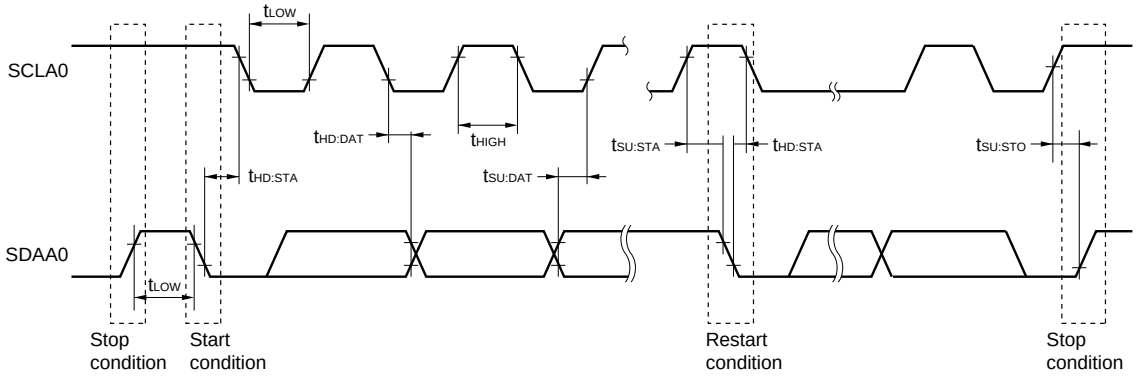
2. The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the $\overline{ACK}$ (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 kΩ

IICA serial transfer timing

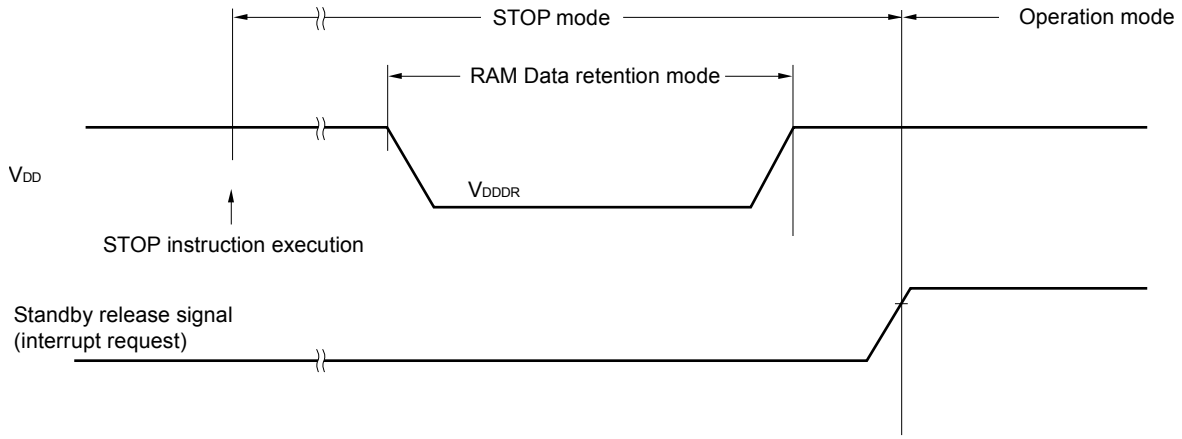


<R>
2.8 RAM Data Retention Characteristics

(T_A = –40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		5.5	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.

<R>


2.9 Flash Memory Programming Characteristics

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	System clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		24	MHz
<R>	Number of code flash rewrites Note 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
<R>	Number of data flash rewrites Note 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
<R>			Retained for 5 years T_A = 85°C	100,000			
<R>			Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.
The retaining years are until next rewrite after the rewrite.
2. When using flash memory programmer and Renesas Electronics self programming library
3. This characteristic indicates the flash memory characteristic and based on Renesas Electronics reliability test.

Remark When updating data multiple times, use the flash memory as one for updating data.

2.10 Dedicated Flash Memory Programmer Communication (UART)

(T_A = –40 to +85°C, 1.8 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During flash memory programming	115,200		1,000,000	bps

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C) (1/3)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V_{DD}	V_{DD} = EV_{DD}	−0.5 to +6.5	V
	EV_{DD}	V_{DD} = EV_{DD}	−0.5 to +6.5	V
	EV_{SS}		−0.5 to +0.3	V
REGC pin input voltage	V_{IREGC}	REGC	−0.3 to +2.8 and −0.3 to V_{DD} + 0.3 Note 1	V
Input voltage	V_{I1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P70 to P74, P120, P125 to P127, P140 to P147	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{I2}	P60, P61 (N-ch open-drain)	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{I3}	P20, P21, P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$	−0.3 to V_{DD} + 0.3 Note 2	V
Output voltage	V_{O1}	P10 to P17, P30 to P32, P40 to P43, P50 to P54, P60, P61, P70 to P74, P120, P125 to P127, P130, P140 to P147	−0.3 to EV_{DD} + 0.3 and −0.3 to V_{DD} + 0.3 Note 2	V
	V_{O2}	P20, P21	−0.3 to V_{DD} + 0.3 Note 2	V
Analog input voltage	V_{AI1}	ANI16 to ANI23	−0.3 to EV_{DD} + 0.3 and −0.3 to AV_{REF}(+) + 0.3 Notes 2, 3	V
	V_{AI2}	ANI0, ANI1	−0.3 to V_{DD} + 0.3 and −0.3 to AV_{REF}(+) + 0.3 Notes 2, 3	V

Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

2. Must be 6.5 V or lower.

3. Do not exceed AV_{REF}(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. AV_{REF}(+) : + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (f_X)Note	Ceramic resonator/ crystal resonator	2.7 V ≤ V_{DD} ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ V_{DD} < 2.7 V	1.0		16.0	MHz
XT1 clock oscillation frequency (f_{XT})Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **3.4 AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

3.2.2 On-chip oscillator characteristics

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f_{IH}			1		24	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–1		+1	%
		–40 to –20°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–1.5		+1.5	%
		+85 to +105°C	2.4 V ≤ V_{DD} ≤ 5.5 V	–2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	f_{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				–15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to **3.4 AC Characteristics** for instruction execution time.

Notes 1. Current flowing to V_{DD}.

2. When high speed on-chip oscillator and high-speed system clock are stopped.

3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.

4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

8. Current flowing only during data flash rewrite.

9. Current flowing only during self programming.

10. For shift time to the SNOOZE mode.

11. Current flowing only to the LCD controller/driver. The supply current value of the RL78 microcontrollers is the sum of the LCD operating current (I_{LCD1}, I_{LCD2} or I_{LCD3}) to the supply current (I_{DD1} or I_{DD2}) when the LCD controller/driver operates in an operation mode or HALT mode. Not including the current that flows through the LCD panel.

The TYP. value and MAX. value are following conditions.

- When f_{SUB} is selected for system clock, LCD clock = 128 Hz (LCDC0 = 07H)
- 4-Time-Slice, 1/3 Bias Method

12. Not including the current that flows through the external divider resistor when the external resistance division method is used.

Remarks 1. f_{IL}: Low-speed on-chip oscillator clock frequency

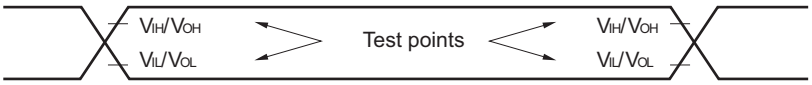
2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

3. f_{CLK}: CPU/peripheral hardware clock frequency

4. Temperature condition of the TYP. value is T_A = 25°C

3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1				f_{MCK}/12	bps
		Theoretical value of the maximum transfer rate f_{MCK} = f_{CLK} Note 2		2.0	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

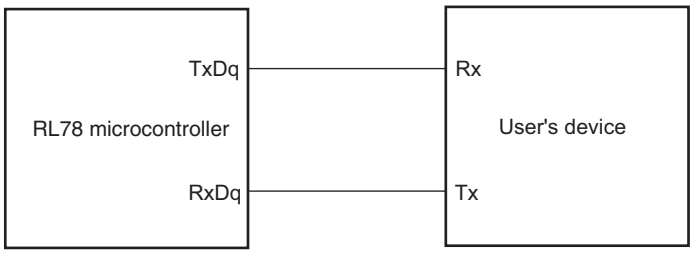
2. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

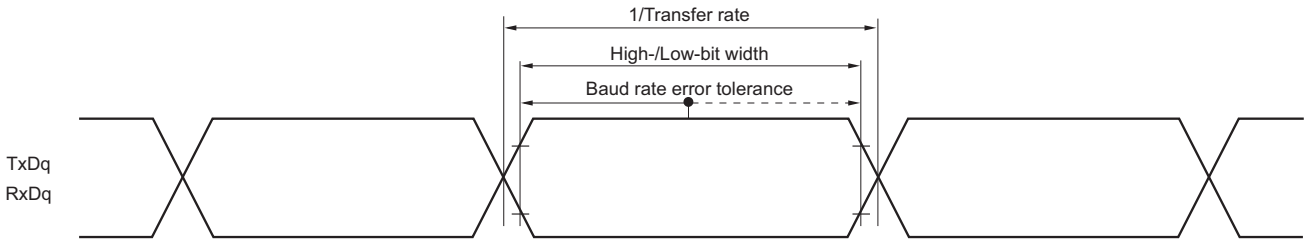
16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0), g: PIM and POM number (g = 1)

2. f_{MCK}: Serial array unit operation clock frequency

(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

(4) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD} = V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS} = 0 V)

Parameter	Symbol	Conditions			HS (high-speed main) Mode		Unit
					MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V			**Note 1**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.0 Note 2	Mbps
			2.7 V ≤ EV_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V			**Note 3**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4	Mbps
			2.4 V ≤ EV_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V			**Note 5**	bps
				Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 6	Mbps

Notes 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

2. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

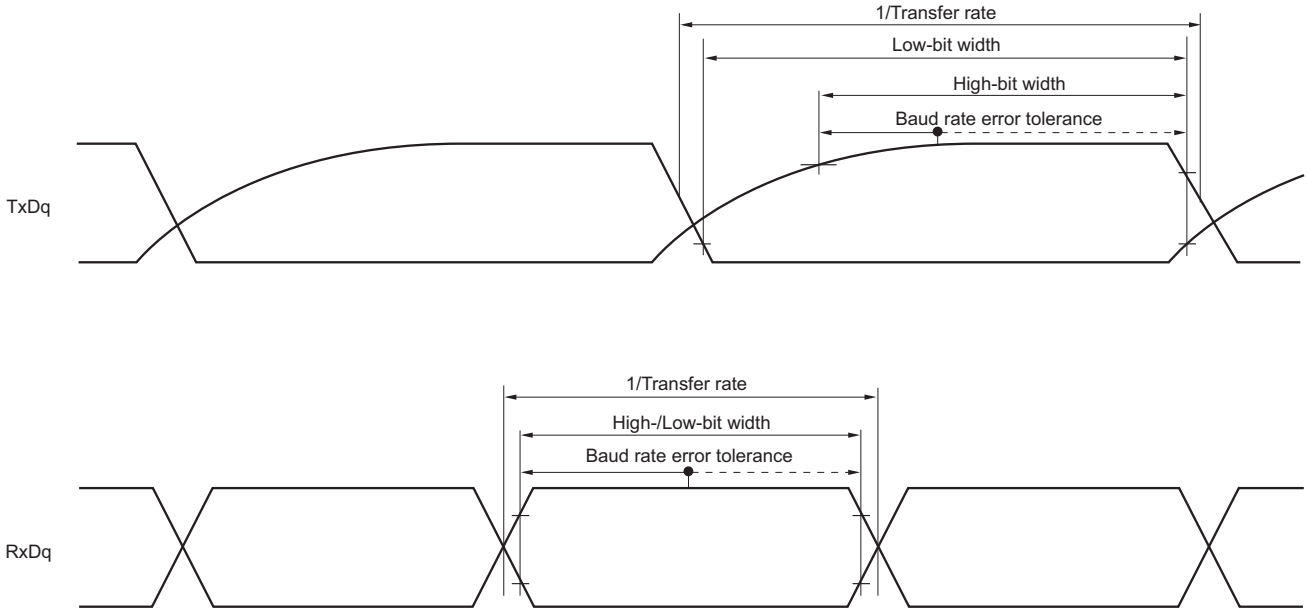
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

4. This value as an example is calculated when the conditions described in the “Conditions” column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

UART mode bit width (during communication at different potential) (reference)



Remarks 1. R_b[Ω]:Communication line (TxDq) pull-up resistance,
C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

2. q: UART number (q = 0, 1), g: PIM and POM number (g = 1)

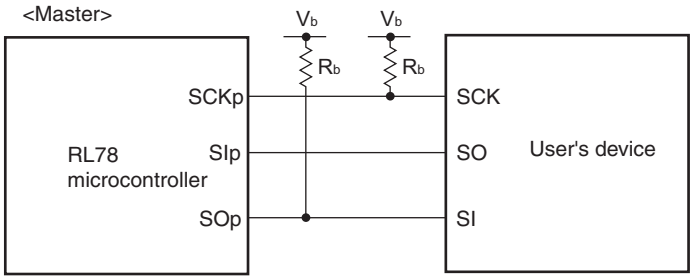
3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01))

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (32- to 52-pin products)/EV_{DD} tolerance (64-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance,
C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

2. p: CSI number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1),
g: PIM and POM number (g = 1)

3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

Rev.	Date	Description	
		Page	Summary
0.01	Feb 20, 2012	-	First Edition issued
0.02	Sep 26, 2012	7, 8	Modification of caution 2 in 1.3.5 64-pin products
		15	Modification of I/O port in 1.6 Outline of Functions
		-	Modification of 2. ELECTRICAL SPECIFICATIONS (TARGET)
		-	Update of package drawings in 3. PACKAGE DRAWINGS
1.00	Jan 31, 2013	11 to 15	Modification of 1.5 Block Diagram
		16	Modification of Note 2 in 1.6 Outline of Functions
		17	Modification of 1.6 Outline of Functions
		-	Deletion of target in 2. ELECTRICAL SPECIFICATIONS
		18	Addition of caution 2 to 2. ELECTRICAL SPECIFICATIONS
		19	Addition of description, note 3, and remark 2 to 2.1 Absolute Maximum Ratings
		20	Modification of description and addition of note to 2.1 Absolute Maximum Ratings
		22, 23	Modification of 2.2 Oscillator Characteristics
		30	Modification of notes 1 to 4 in 2.3.2 Supply current characteristics
		32	Modification of notes 1, 3 to 6, 8 in 2.3.2 Supply current characteristics
		34	Modification of notes 7, 9, 11, and addition of notes 8, 12 to 2.3.2 Supply current characteristics
		36	Addition of description to 2.4 AC Characteristics
		38, 40 to 42, 44 to 46, 48 to 52, 54, 55	Modification of 2.5.1 Serial array unit
		57, 58	Modification of 2.5.2 Serial interface IICA
		62	Modification of 2.6.2 Temperature sensor/internal reference voltage characteristics
		64	Addition of note and caution in 2.6.5 Supply voltage rise time
		69	Modification of 2.8 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics
		69	Modification of conditions in 2.9 Timing Specs for Switching Flash Memory Programming Modes
		70	Modification of 2.10 Timing Specifications for Switching Flash Memory Programming Modes
2.00	Jan 10, 2014	1	Modification of 1.1 Features
		3	Modification of Figure 1-1
		4	Modification of part number, note, and caution
		5 to 10	Deletion of COMEXP pin in 1.3.1 to 1.3.5.
		11	Modification of description in 1.4 Pin Identification
		12 to 16	Deletion of COMEXP pin in 1.5.1 to 1.5.5
		17	Modification of table and note 2 in 1.6 Outline of Functions
		20	Modification of description in Absolute Maximum Ratings (T_A = 25°C) (1/3)
		21	Modification of description and note 2 in Absolute Maximum Ratings (T_A = 25°C) (2/3)
		23	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics
		23	Modification of table in 2.2.2 On-chip oscillator characteristics
		24	Modification of table, notes 2 and 3 in 2.3.1 Pin characteristics (1/5)
		25	Modification of notes 1 and 3 in 2.3.1 Pin characteristics (2/5)
		30	Modification of notes 1 and 4 in 2.3.2 Supply current characteristics (1/3)
		31, 32	Modification of table, notes 1, 5, and 6 in 2.3.2 Supply current characteristics (2/3)
		33, 34	Modification of table, notes 1, 3, 4, and 5 to 10 in 2.3.2 Supply current characteristics (3/3)

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